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**Patent Abstracts of Japan**

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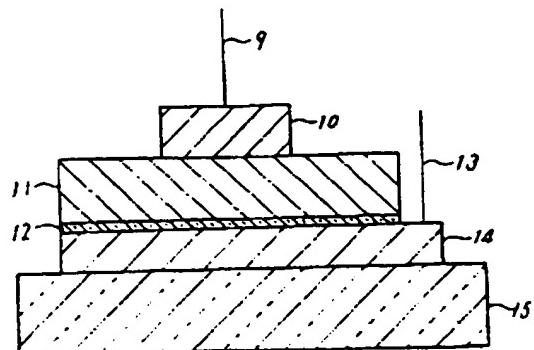
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TITLE : MANUFACTURE OF MIS DIODE



**ABSTRACT :** PURPOSE: To obtain high and stable performance by forming an insulating organic layer on a metal electrode by electrolytic polymerizing method, forming a semiconductor layer thereon, and further forming a conductive layer to become an electrode thereon.

CONSTITUTION: An Al electrode 14 is formed on a glass substrate 15 as an operating electrode. A poly  $\alpha$ -naphthole layer 12 is precipitated as an insulating organic polymer layer on the electrode to obtain an insulating organic polymer sample. A poly N-methylpyrrole film 11 is precipitated as a  $\pi$ -conjugate polymer layer on the sample, and an Au electrode 10 is formed on the film 11. A MIS diode having high performance and stable performance can be readily formed by the above manufacturing method.

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